

Schottky barrier diode

RB530XN

●Applications

Rectifying small power

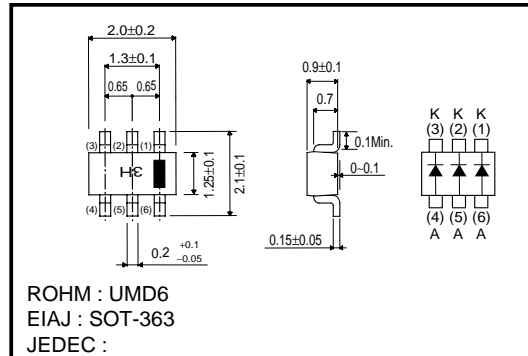
●Features

- 1) Small mold type. (UMD6)
- 2) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current *1	I_O	100	mA
Peak forward surge current *2	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

*1 Rating of per diode.

*2 60Hz for 1 \varnothing

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	–	–	0.400	V	$I_F=10\text{mA}$
	V_{F2}	–	–	0.530	V	$I_F=100\text{mA}$
Reverse current	I_R	–	–	1.0	μA	$V_R=10\text{V}$

Note) Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

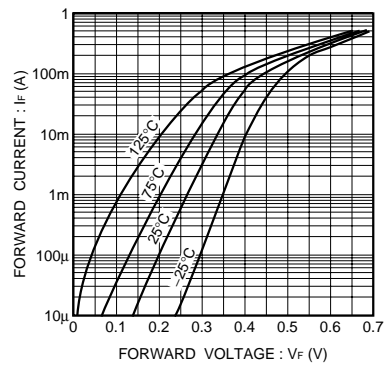


Fig.1 Forward characteristics

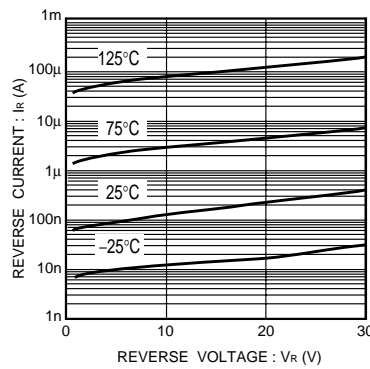


Fig.2 Reverse characteristics

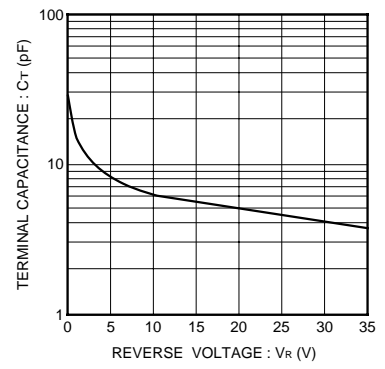


Fig.3 Capacitance between terminals characteristics